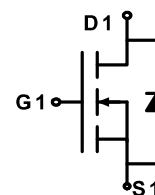


AP2012S

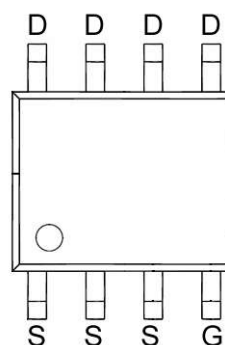
N-Channel Power MOSFET

Description

The AP2012S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications .



Schematic diagram



pin assignment



General Features

- $V_{DS} = 20V, I_D = 12A$
 $R_{DS(ON)} < 11m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 14m\Omega @ V_{GS}=2.5V$
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Uni-directional load switch
- Bi-directional load switch

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	12	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	45	A
Maximum Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	62.5	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA

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Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.7	1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=5A$	-	9	11	m Ω
		$V_{GS}=2.5V, I_D=4A$	-	12	14	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=8A$	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	1800	-	PF
Output Capacitance	C_{oss}		-	230	-	PF
Reverse Transfer Capacitance	C_{rss}		-	200	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1.2\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	2.5		nS
Turn-on Rise Time	t_r		-	7.2		nS
Turn-Off Delay Time	$t_{d(off)}$		-	49		nS
Turn-Off Fall Time	t_f		-	10.8		nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=8A,$ $V_{GS}=4.5V$	-	17.9		nC
Gate-Source Charge	Q_{gs}		-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	4.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	12	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

N-Channel Power MOSFET

Typical Electrical and Thermal Characteristics

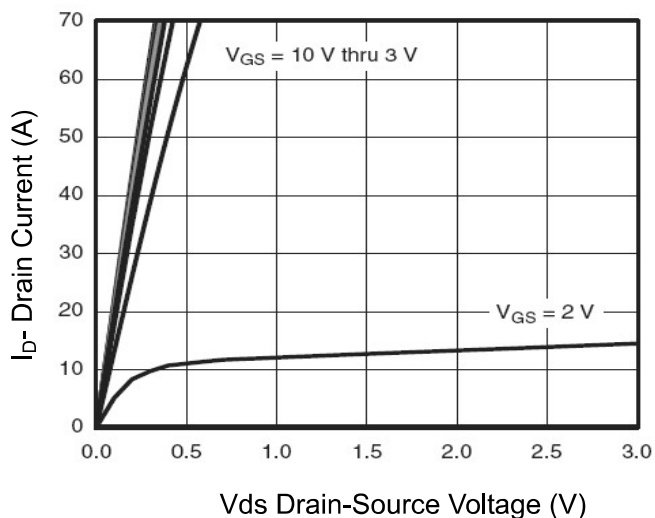


Figure 1 Output Characteristics

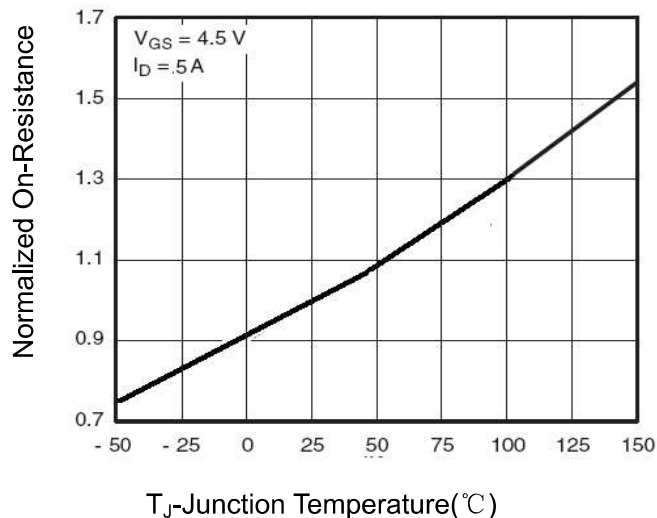


Figure 2 R_{dson} -Junction Temperature

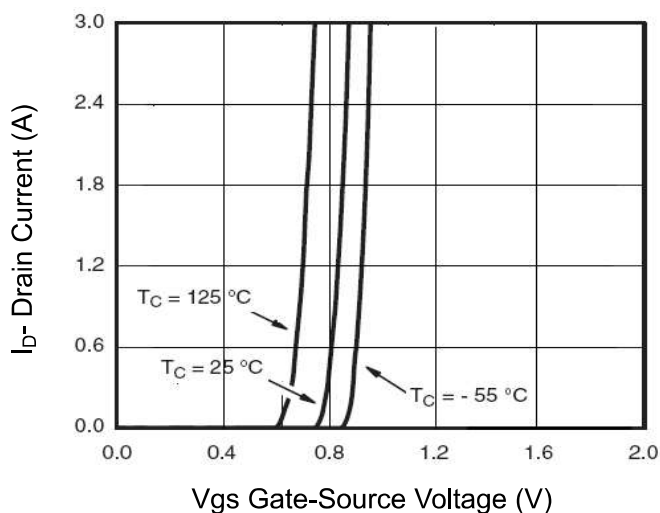


Figure 3 Transfer Characteristics

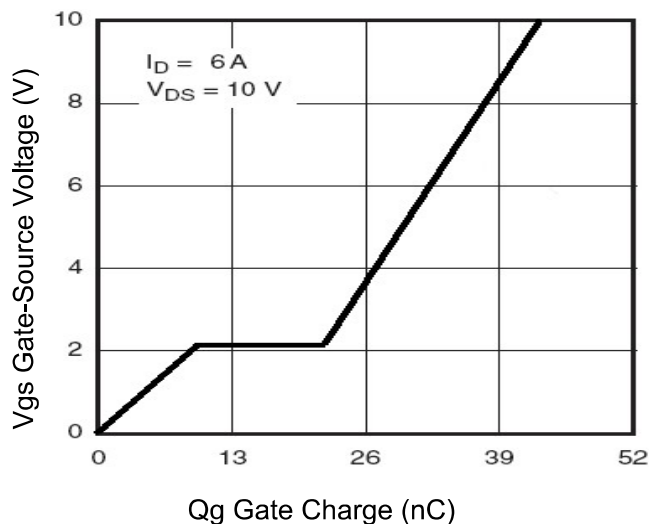


Figure 4 Gate Charge

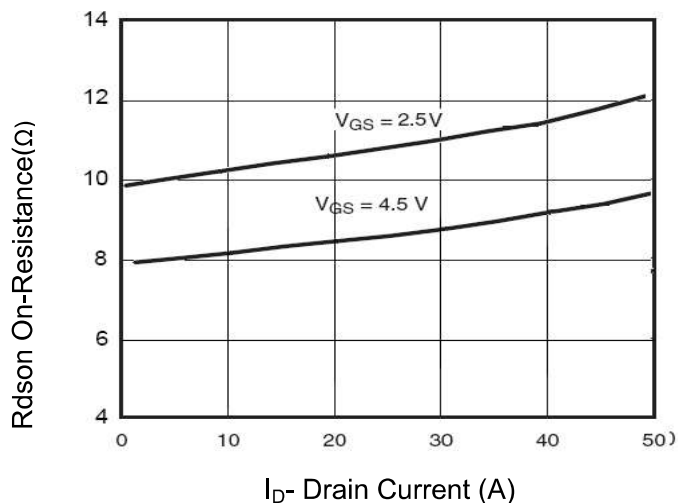


Figure 5 R_{dson} - Drain Current

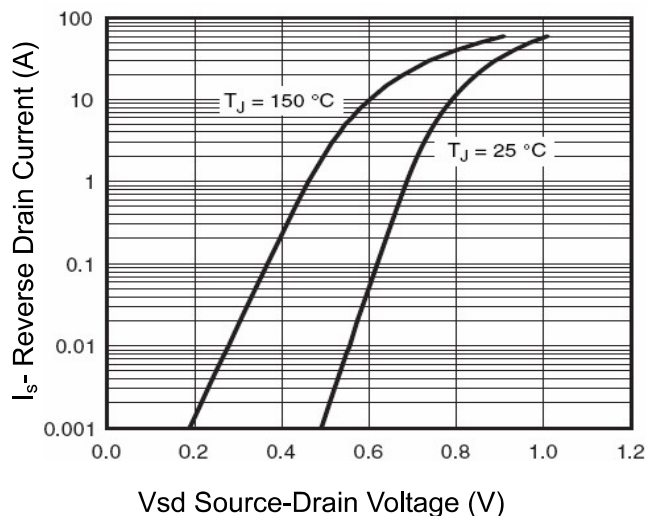


Figure 6 Source- Drain Diode Forward

AP2012S

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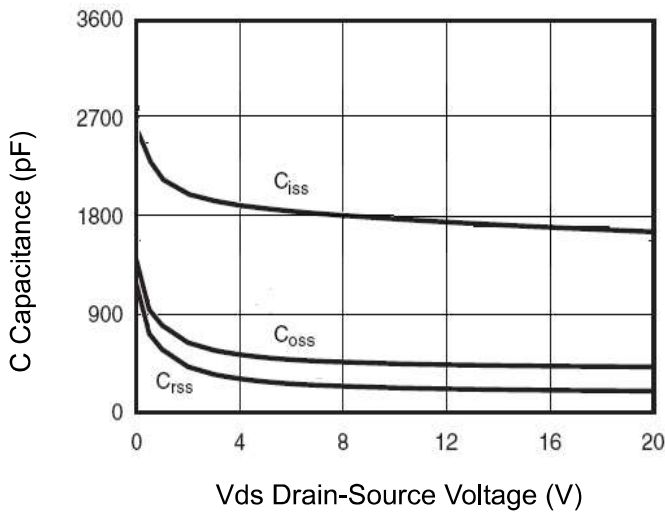


Figure 7 Capacitance vs Vds

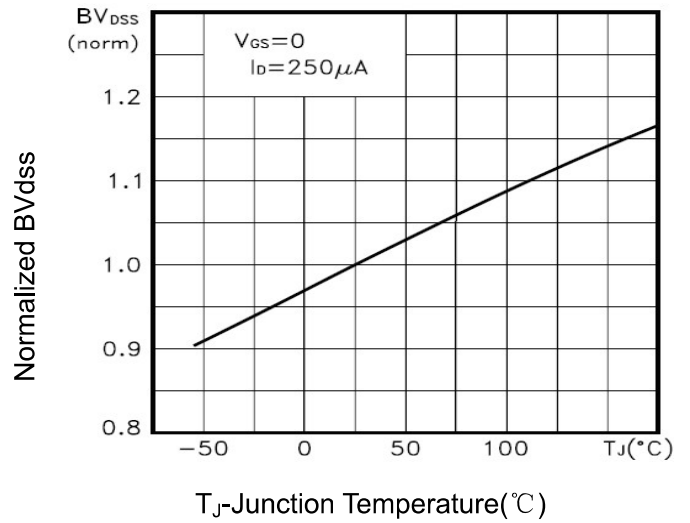


Figure 8 BV_{DSS} vs Junction Temperature

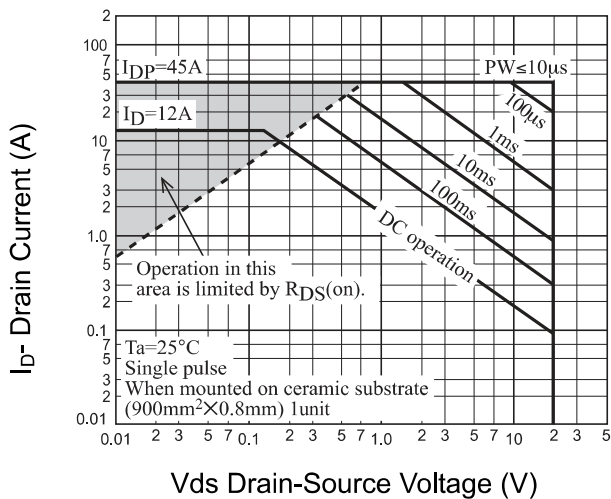


Figure 9 Safe Operation Area

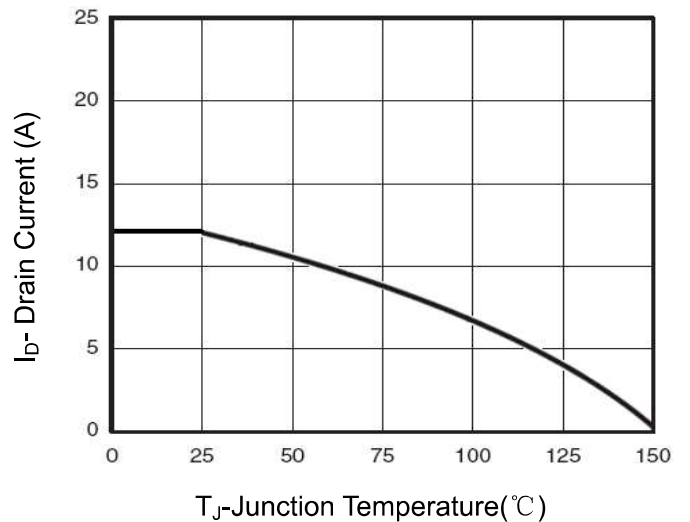


Figure 10 Current vs Junction Temperature

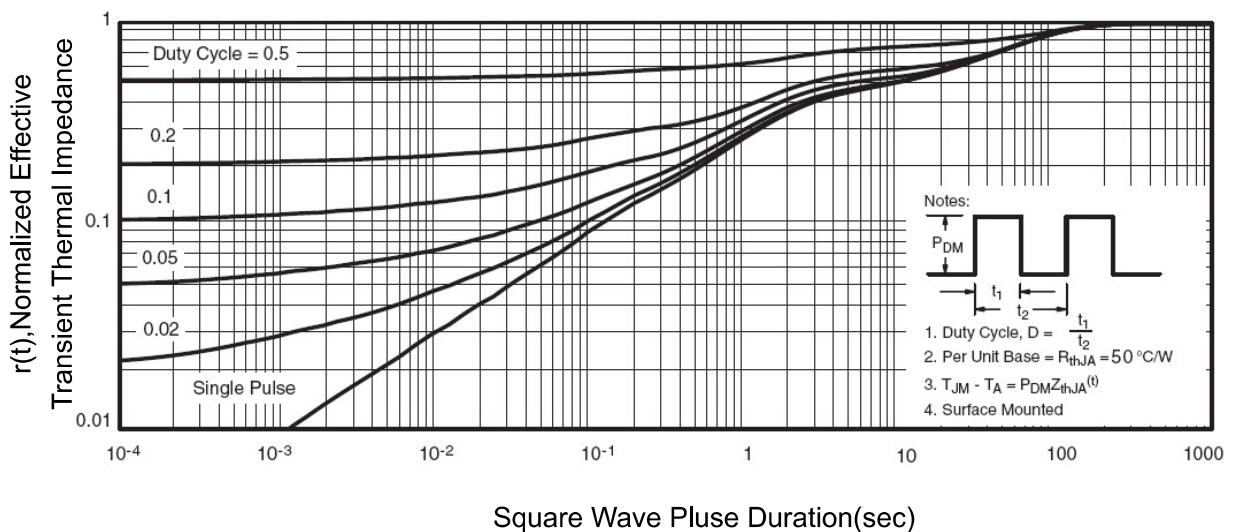


Figure 11 Normalized Maximum Transient Thermal Impedance

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外形尺寸图 / Package Dimensions

SOP-8

Unit:mm

